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U.S. PATENT DOCUMENTS							
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FOREIGN PATENT DOCUMENTS							
		Document No.	Date	Country	Class	Subclass	Translation
MS	F	2 757 183	6/1998	France	C30B	33/108	No
	G	/					
	H						
	I						

OTHER REFERENCES <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
M>	J	Patent Abstract of Japan, Vol. 016, No. 362 (C-0971), 5 Aug. 1992, & JP 04 114995 A (Matsushita Electric Ind. Co. Ltd.), 15 April 1992
M)	K	Patent Abstracts of Japan, Vol. 016, No. 329 (C-0963), 17 July 1992, & JP 04 092893 A (Fuain Seramitsukusu Sentaa), 25 March 1992
m>	L	Kackell, P. et al.: "Polytypism and Surface Structure of SiC"; Diamond and Related Materials, vol. 6, No. 10, 1 August 1997, pg. 1346-1348 XP004096938 ISSN: 0925-9635
m)	M	Kawarada H. et al.: "Heteroepitaxial Growth of Smooth and Continuous Diamond Thin Films on Silicon Substrates Via High Quality Silicon Carbide Buffer Layerse", Applied Physics Letters, Vo. 66, No. 5 30 January 1995, pgs. 583-585, XP000489804 ISSN: 0003-6951

Examiner: <i>Mark Song Matthew Song</i>	Date Considered: <i>8/5/2002</i>
*Examiner: Initial if reference considered, regardless of whether citation is in conformance with MPEP 609; Draw line through citation if not in conformance <u>and</u> not considered. Include copy of this form with next communication to applicant.	

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U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
33585SERIAL NO.
09/856,211INFORMATION DISCLOSURE CITATION
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APPLICANT:

Vincent Derycke et al.

FILING DATE:
5/18/2001GROUP/ART UNIT:
1765

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Examiner Initial		Document No.	Date	Name	Class	Subclass	Filing Date If Appropriate
	A	6,274,234	8/2001	Dujardin et al.	428	336	

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